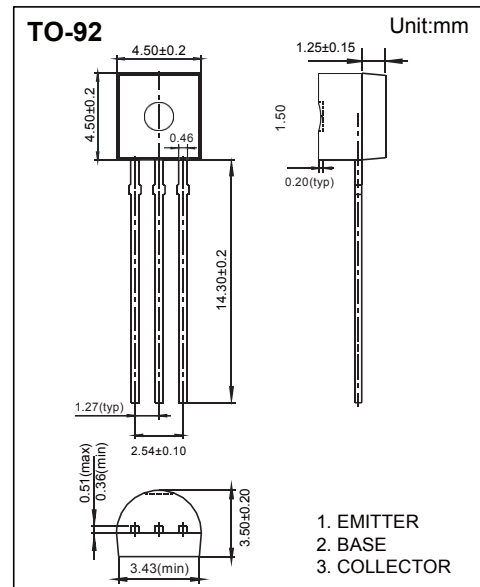


## PNP General Purpose Transistor BC327

### ■ Features

- High current (max. 500 mA)
- Low voltage (max. 45 V).



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	-50	V
Collector - Emitter Voltage	$V_{CEO}$	-45	
Emitter - Base Voltage	$V_{EBO}$	-5	
Collector Current - Continuous	$I_C$	-500	mA
Peak Collector Current	$I_{CM}$	-1	A
Peak Base Current	$I_{BM}$	-200	mA
Collector Power Dissipation	$P_C$	625	mW
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	0.2	K/mW
Junction Temperature	$T_J$	150	°C
Operating Ambient Temperature	$T_{amb}$	-65 to 150	
Storage Temperature range	$T_{stg}$	-65 to 150	

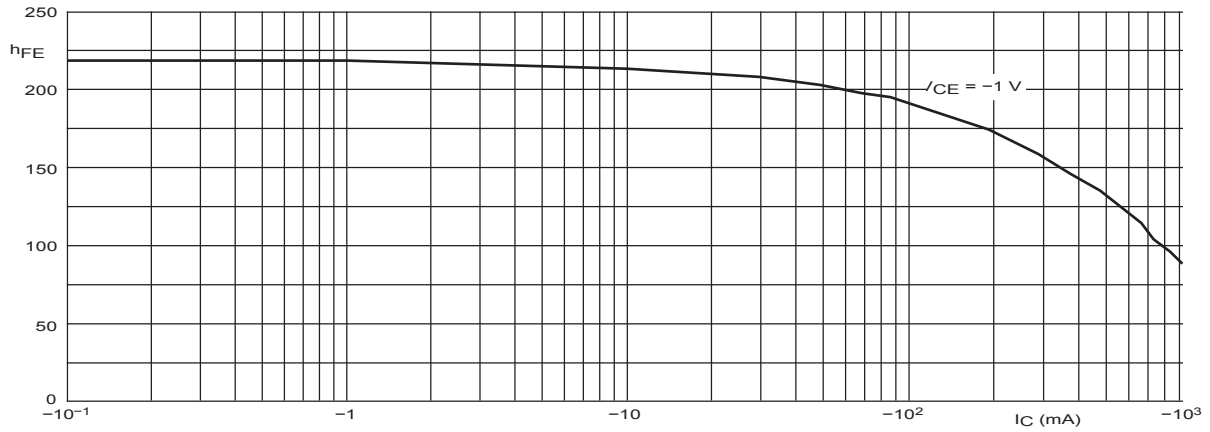
## PNP General Purpose Transistor BC327

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = -100 μA, I <sub>E</sub> =0	-50			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1 mA, I <sub>B</sub> =0	-45			
Emitter - base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = -100 μA, I <sub>C</sub> =0	-5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -20 V, I <sub>E</sub> =0			-100	nA
		V <sub>CB</sub> = -20 V, I <sub>E</sub> =0, T <sub>J</sub> = 25°C			-5	μA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-100	nA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA			-0.7	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA			-1.2	
Base - emitter voltage	V <sub>BE</sub>	I <sub>C</sub> = -500 mA, V <sub>CE</sub> = -1V			-1.2	
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> =-100mA	100		600	
			100		250	
			160		400	
			250		600	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> =-500mA see Figs 1, 2 and 3	40			
Collector capacitance	C <sub>ob</sub>	I <sub>E</sub> =I <sub>E</sub> =0, V <sub>CB</sub> =-10V, f=1MHz		10		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f=100MHz	80			MHz

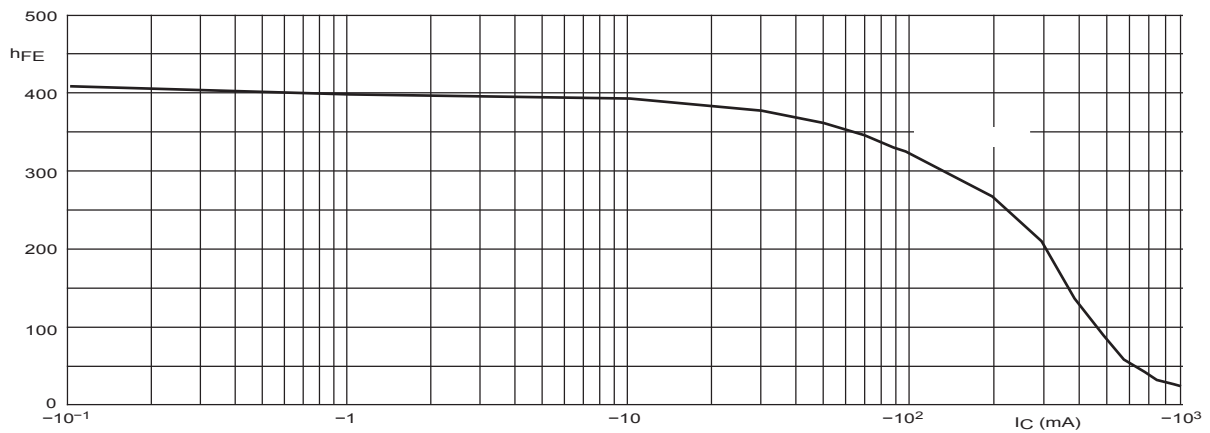
## PNP General Purpose Transistor BC327

■ Typical Characteristics



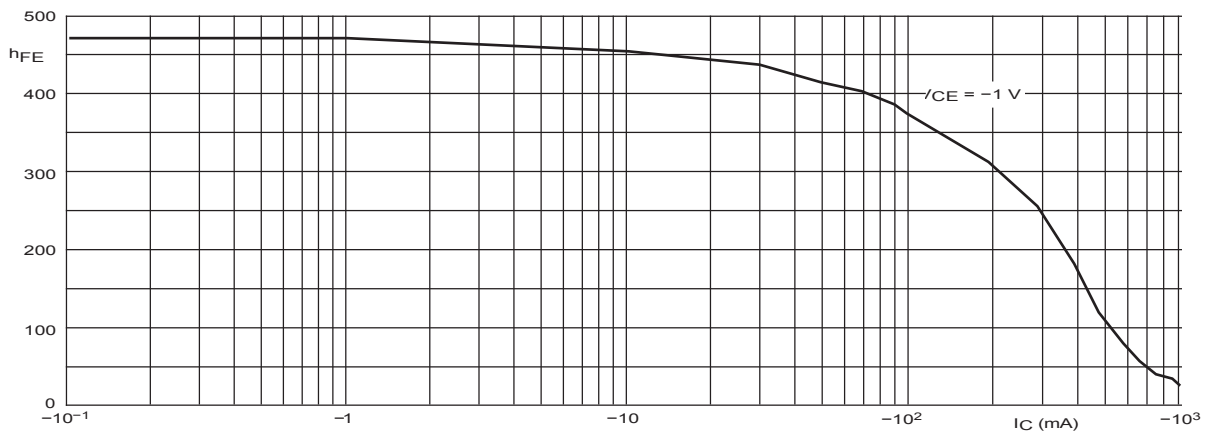
BC327-16.

Fig.1 DC current gain; typical values.



BC327-25.

Fig.2 DC current gain; typical values.



BC327-40.

Fig.3 DC current gain; typical values.